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Kind regards,

Team Nexperia

ES1DVR

200 V, 1 A hyperfast PN-rectifier

12 January 2017 **Product data sheet**

1. General description

High power density, hyperfast PN-rectifier with high-efficiency planar technology, encapsulated in a small and flat lead SOD123W Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- Reverse voltage $V_R \leq 200$ V
- Forward current $I_F \leq 1$ A
- Hyperfast recovery time $t_{rr} \leq 25$ ns
- Pt doped life time control
- Low inductance
- Small and flat lead SMD plastic package
- Package height typ. 1 mm
- High power capability due to clip-bond technology
- Planar die design

3. Applications

- General-purpose rectification
- Reverse polarity protection
- Hyperfast switching
- Freewheeling applications

4. Quick reference data

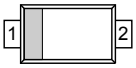
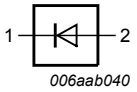
Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$I_{F(AV)}$	average forward current	$\delta = 0.5$; f = 20 kHz; square wave; $T_{sp} \leq$ 145 °C		-	-	1	A
V_{RRM}	repetitive peak reverse voltage	T_j = 25 °C		-	-	200	V
V_R	reverse voltage			-	-	200	V
V_F	forward voltage	I_F = 1 A; pulsed; T_j = 25 °C	[1]	-	820	875	mV
		I_F = 1 A; pulsed; T_j = 125 °C	[1]	-	675	750	mV
I_R	reverse current	V_R = 200 V; pulsed; T_j = 25 °C	[1]	-	5	200	nA
		V_R = 200 V; pulsed; T_j = 125 °C	[1]	-	1.5	20	µA

[1] Very short test pulse to keep the junction temperature unchanged.

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	 SOD123W	 006aab040
2	A	anode		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
ES1DVR	SOD123W	plastic surface mounted package; 2 leads	SOD123W

7. Marking

Table 4. Marking codes

Type number	Marking code
ES1DVR	KK

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage	T_j = 25 °C		-	200	V
V_R	reverse voltage			-	200	V
V_{RMS}	RMS voltage			-	140	V
I_F	forward current	δ = 1 ; T_{sp} ≤ 143 °C		-	1.4	A
$I_{F(AV)}$	average forward current	δ = 0.5 ; f = 20 kHz; square wave; T_{sp} ≤ 145 °C		-	1	A
I_{FSM}	non-repetitive peak forward current	t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; single half sine wave (applied at rated load condition)		-	40	A
P_{tot}	total power dissipation	T_{amb} ≤ 25 °C	[1]	-	735	mW
			[2]	-	1.19	W
T_j	junction temperature			-	150	°C
T_{amb}	ambient temperature			-55	150	°C
T_{stg}	storage temperature			-65	150	°C

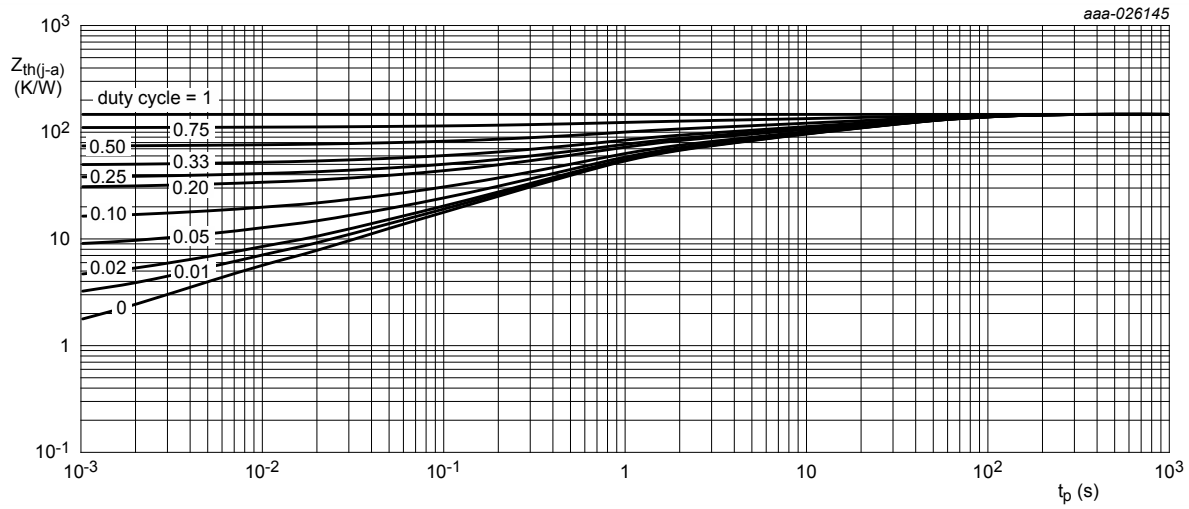
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm^2.

9. Thermal characteristics

Table 6. Thermal characteristics

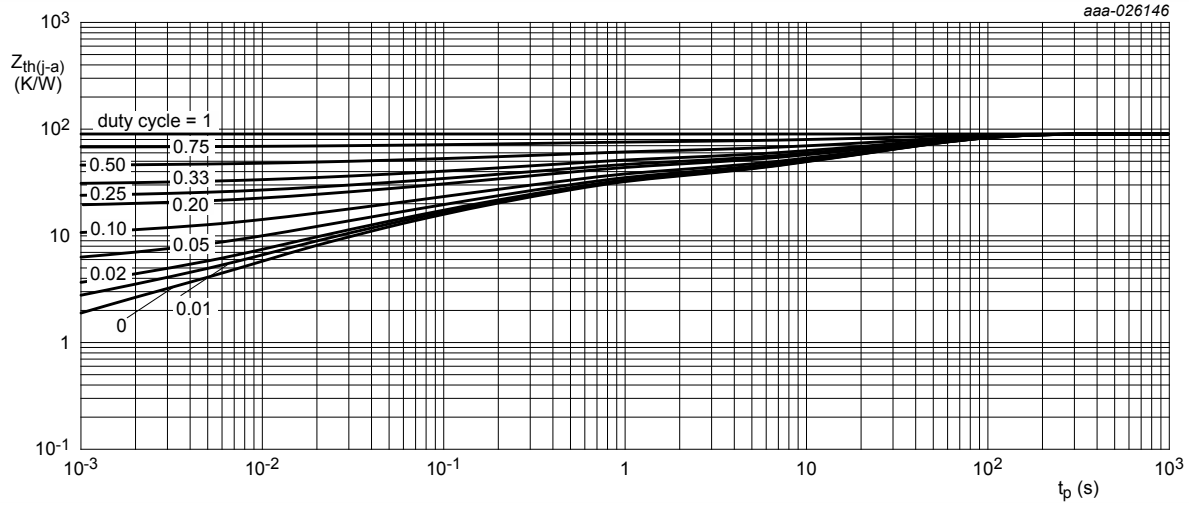
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	170	K/W
			[2]	-	-	105	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		[3]	-	-	15	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm^2.
[3] Soldering point of cathode tab.



FR4 PCB, standard footprint

Fig. 1. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for cathode 1 cm^2

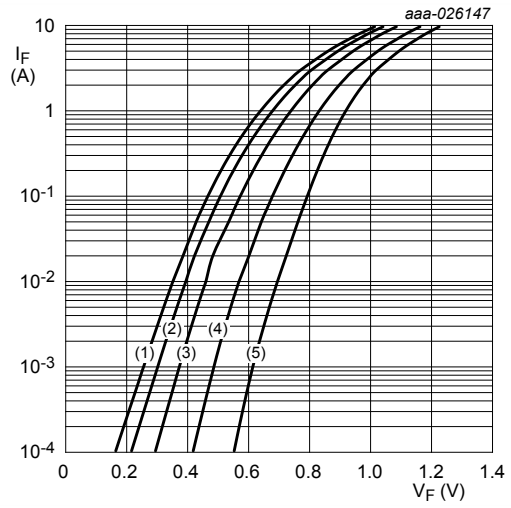
Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

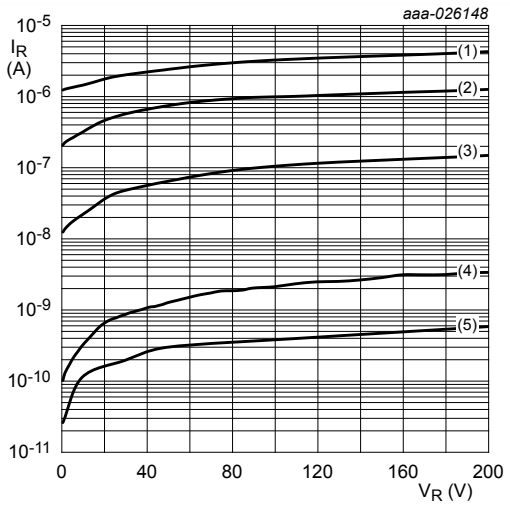
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$V_{(BR)R}$	reverse breakdown voltage	I_R = 100 µA; T_j = 25 °C; pulsed	[1]	200	-	-	V
V_F	forward voltage	I_F = 1 A; pulsed; T_j = 25 °C	[1]	-	820	875	mV
		I_F = 1 A; pulsed; T_j = 125 °C	[1]	-	675	750	mV
I_R	reverse current	V_R = 200 V; pulsed; T_j = 25 °C	[1]	-	5	200	nA
		V_R = 200 V; pulsed; T_j = 125 °C	[1]	-	1.5	20	µA
C_d	diode capacitance	f = 1 MHz; V_R = 4 V; T_j = 25 °C		-	20	-	pF
t_{rr}	reverse recovery time ; step recovery	I_F = 0.5 A; I_R = 1 A; $I_{R(meas)}$ = 0.25 A; T_j = 25 °C		-	10	25	ns
	reverse recovery time ; ramp recovery	I_F = 1 A; dI_F/dt = 50 A/µs; V_R = 30 V; T_j = 25 °C		-	20	-	ns
V_{FRM}	peak forward recovery voltage	I_F = 1 mA; dI_F/dt = 50 A/µs; T_j = 25 °C		-	930	-	mV

[1] Very short test pulse to keep the junction temperature unchanged.



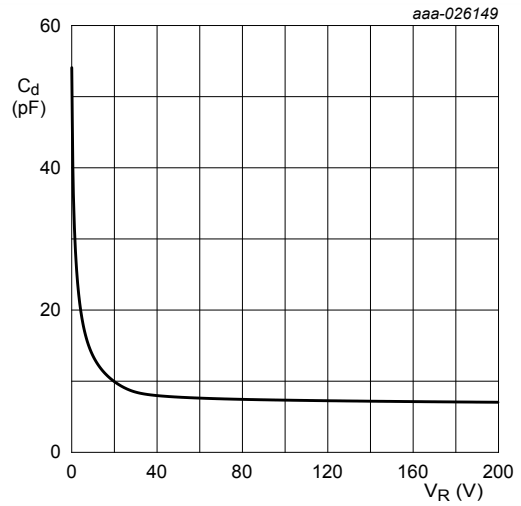
pulsed condition
(1) T_j = 150 °C
(2) T_j = 125 °C
(3) T_j = 85 °C
(4) T_j = 25 °C
(5) T_j = -40 °C

Fig. 3. Forward current as a function of forward voltage; typical values



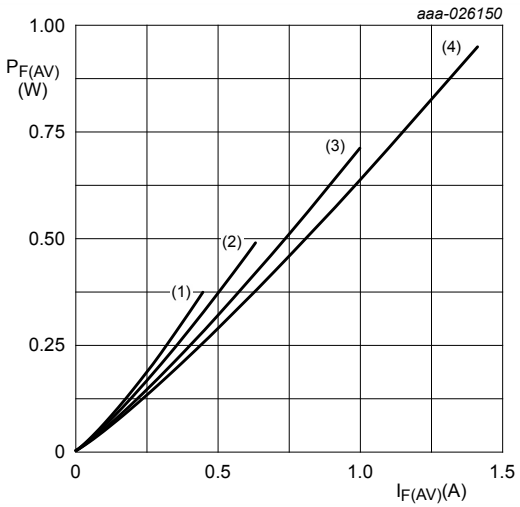
pulsed condition
(1) T_j = 150 °C
(2) T_j = 125 °C
(3) T_j = 85 °C
(4) T_j = 25 °C
(5) T_j = −40 °C

Fig. 4. Reverse current as a function of reverse voltage; typical values



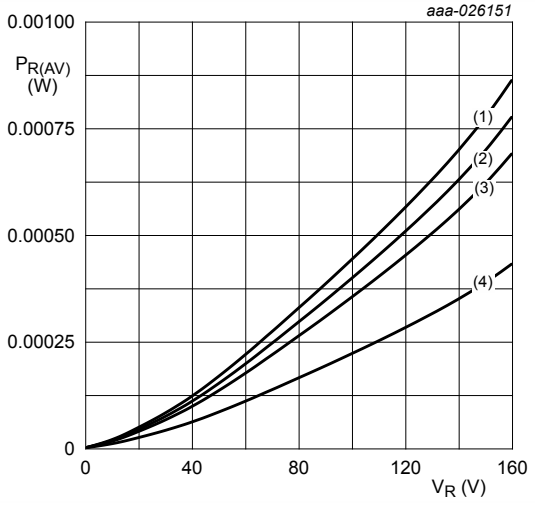
f = 1 MHz; T_{amb} = 25 °C

Fig. 5. Diode capacitance as a function of reverse voltage; typical values



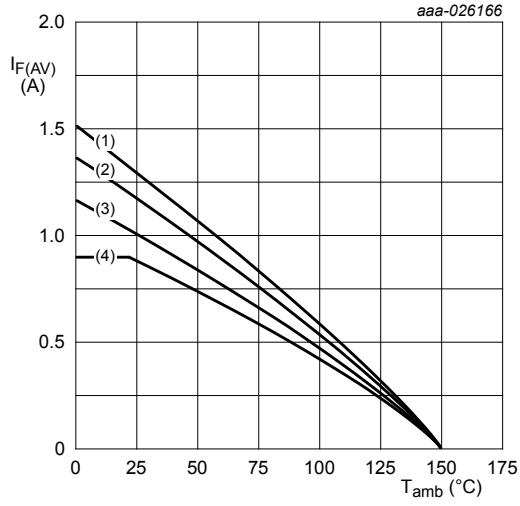
T_j = 150 °C
(1) δ = 0.1
(2) δ = 0.2
(3) δ = 0.5
(4) δ = 1

Fig. 6. Average forward power dissipation as a function of average forward current; typical values



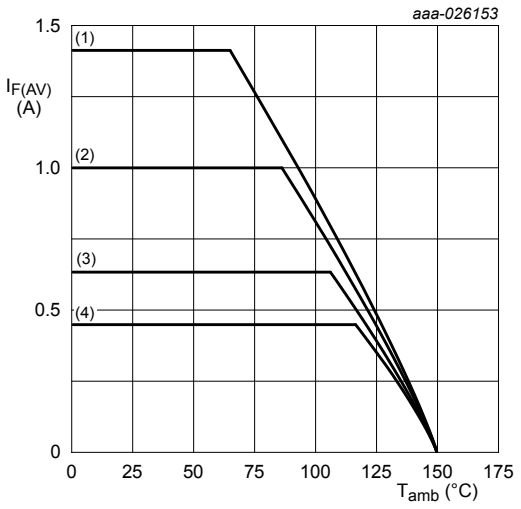
T_j = 150 °C
(1) δ = 1
(2) δ = 0.9
(3) δ = 0.8
(4) δ = 0.5

Fig. 7. Average reverse power dissipation as a function of reverse voltage; typical values



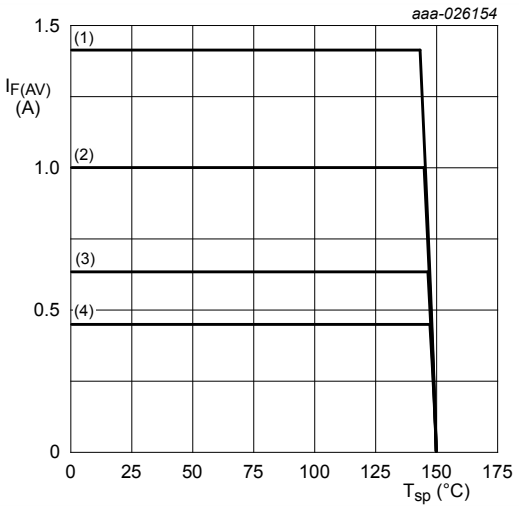
FR4 PCB, standard footprint
T_j = 150 °C
(1) δ = 1; DC
(2) δ = 0.5; f = 20 kHz
(3) δ = 0.2; f = 20 kHz
(4) δ = 0.1; f = 20 kHz

Fig. 8. Average forward current as a function of ambient temperature; typical values



FR4 PCB, mounting pad for cathode 1 cm^2
T_j = 150 °C
(1) δ = 1; DC
(2) δ = 0.5; f = 20 kHz
(3) δ = 0.2; f = 20 kHz
(4) δ = 0.1; f = 20 kHz

Fig. 9. Average forward current as a function of ambient temperature; typical values



T_j = 150 °C
(1) δ = 1; DC
(2) δ = 0.5; f = 20 kHz
(3) δ = 0.2; f = 20 kHz
(4) δ = 0.1; f = 20 kHz

Fig. 10. Average forward current as a function of solder point temperature; typical values

11. Test information

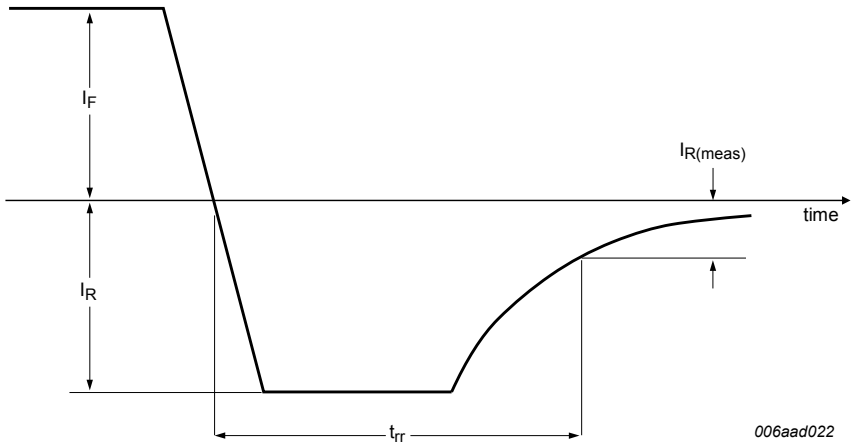


Fig. 11. Reverse recovery definition; step recovery

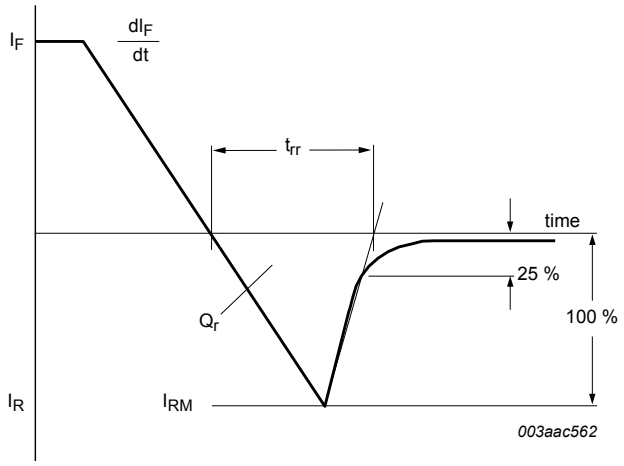


Fig. 12. Reverse recovery definition; ramp recovery

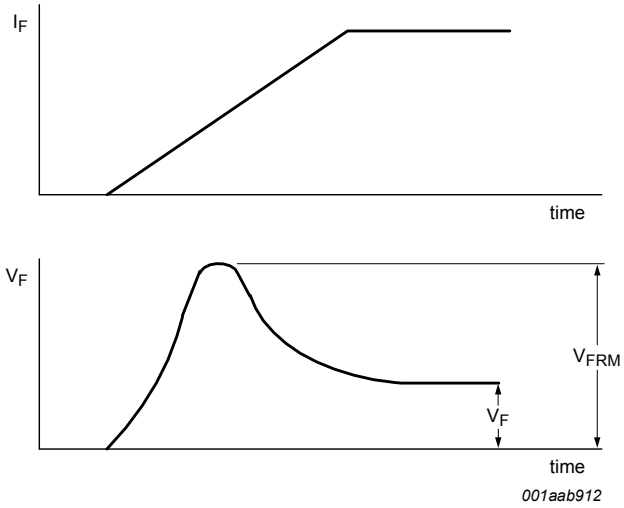


Fig. 13. Forward recovery definition

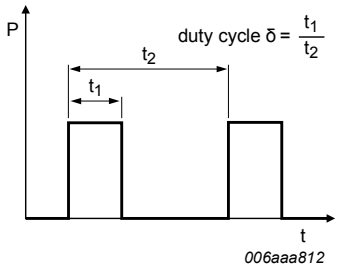


Fig. 14. Duty cycle definition

The current ratings for the typical waveforms are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

12. Package outline

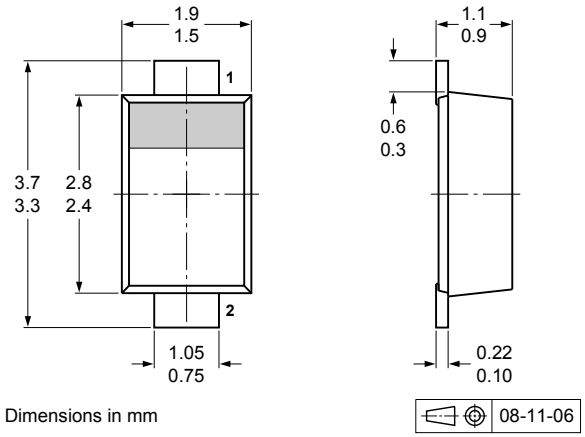


Fig. 15. Package outline SOD123W

13. Soldering

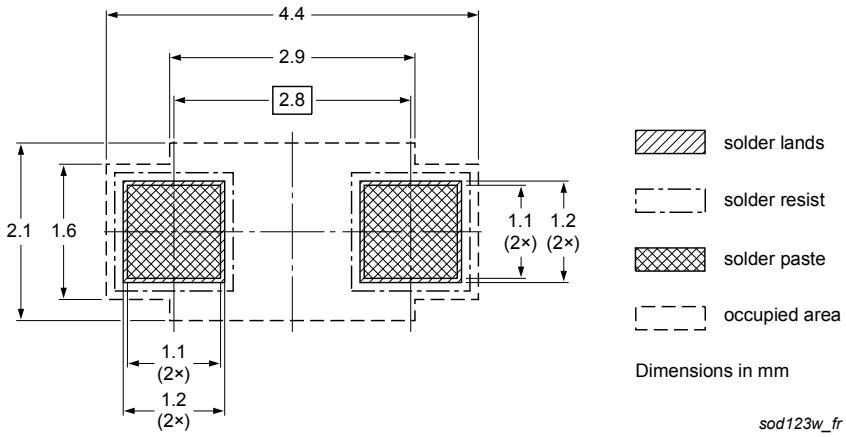


Fig. 16. Reflow soldering footprint for SOD123W

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
ES1DVR v.2	20170112	Product data sheet	-	ES1DVR v.1
Modifications:	• Product status changed			
ES1DVR v.1	20160930	Objective data sheet	-	-

15. Legal information

Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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